# imall

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# Contact us

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#### N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

#### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C
	52mΩ @ V <sub>GS</sub> = 10V	4A
30V	65mΩ @ V <sub>GS</sub> = 4.5V	ЗA
	85mΩ @ V <sub>GS</sub> = 2.5V	2A

## Applications

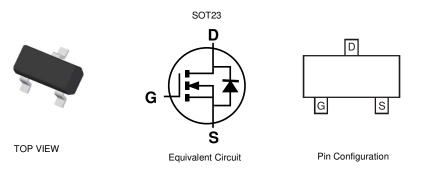
- DC-DC Converters
- Power Management Functions
- Battery Operated Systems and Solid-State Relays

#### **Features**

- Low On-Resistance:
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 3
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)



#### Ordering Information (Note 4)

Part Number	Case	Packaging
DMG3402L-7	SOT23	3000/Tape & Reel
DMG3402L-13	SOT23	10000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://:www.diodes.com/products/packages.html.

## **Marking Information**

I	<b>N</b> 32	ΥM

N32 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: T = 2006)

M = Month (ex: 9 = September)

Date Code Key

	1											
Year	201	2	2013		2014	20	15	2016		2017	2	2018
Code	Z		А		В	(	2	D		E		F
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



#### **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain Source Voltage	V <sub>DSS</sub>	30	V
Gate-Source Voltage	V <sub>GSS</sub>	±12	V
Drain Current (Note 5)	I <sub>D</sub>	4.0	А
Body-Diode Continuous Current (Note 5)	ls	1.5	A

# **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	PD	1.4	W
Thermal Resistance, Junction to Ambient $@T_A = +25^{\circ}C$ (Note 5)	R <sub>0JA</sub>	90	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C

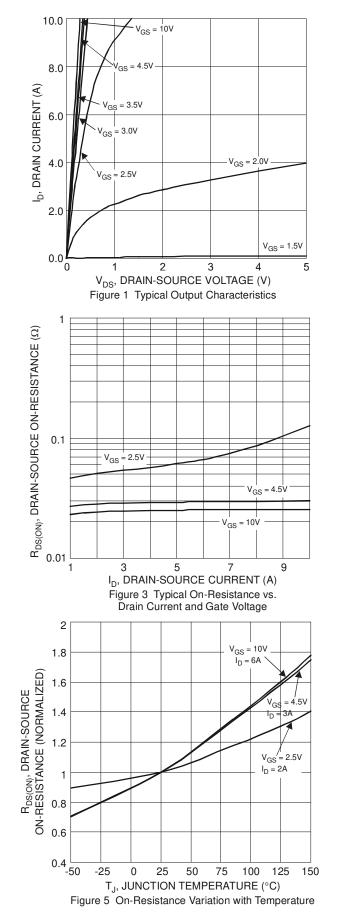
#### **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

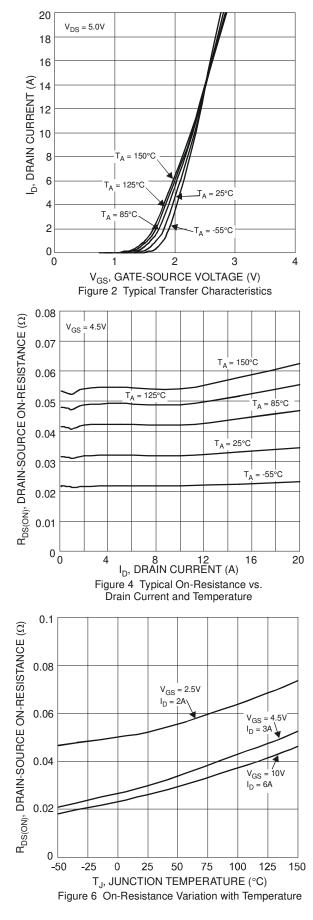
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 6)								
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	_		V	$V_{GS} = 0V, I_D = 250 \mu A$		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μA	$V_{DS} = 30V, V_{GS} = 0V$		
Gate-Body Leakage	IGSS	_	_	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$		
ON CHARACTERISTICS (Note 6)								
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.6	—	1.4	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$		
			—	52		$V_{GS} = 10V, I_D = 4A$		
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	—	65	mΩ	$V_{GS}=4.5V,I_{D}=3A$		
			—	85		$V_{GS} = 2.5V, I_D = 2A$		
Forward Transconductance	Y <sub>fs</sub>	_	6.6		S	$V_{DS} = 5V, I_D = 3.1A$		
Source-Drain Diode Forward Voltage	V <sub>SD</sub>	_	—	1.16	V	$V_{GS} = 0V, I_{S} = 2.0A$		
DYNAMIC CHARACTERISTICS(Note 7)								
Gate Resistance	Rg	_	2.2	—	Ω	$V_{DS} = 0V, V_{GS} = 0V,$ f = 1MHz		
Total Gate Charge (10V)	Qg		11.7		nC	$\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \ V, \ V_{DS} = 15 V, \\ I_D = 4 \ A \end{array}$		
Total Gate Charge (4.5V)	Qq	_	5.5		nC			
Gate-Source Charge	Q <sub>gs</sub>	_	1.1		nC	$V_{GS} = 10 V, V_{DS} = 15V,$		
Gate-Drain Charge	Q <sub>gd</sub>	_	1.8		nC	$I_D = 4 A$		
Turn-On Delay Time	t <sub>D(on)</sub>		1.9		ns			
Turn-On Rise Time	tr	_	1.6		ns	$V_{DD} = 15V, V_{GEN} = 10V,$		
Turn-Off Delay Time	t <sub>D(off)</sub>		10.3		ns	$R_{GEN} = 3\Omega, R_L = 3.75\Omega$		
Turn-Off Fall Time	tf		2.0		ns	]		
Input Capacitance	C <sub>iss</sub>		464		pF			
Output Capacitance	Coss	_	49.5		pF	$V_{DS} = 15V, V_{GS} = 0V$		
Reverse Transfer Capacitance	C <sub>rss</sub>	_	43.8		pF	f = 1.0MHz		

Notes:

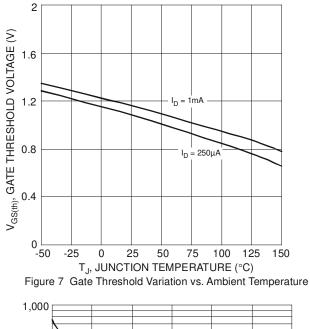
Device mounted on FR-4 PCB. t ≤5 sec.
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to production testing.

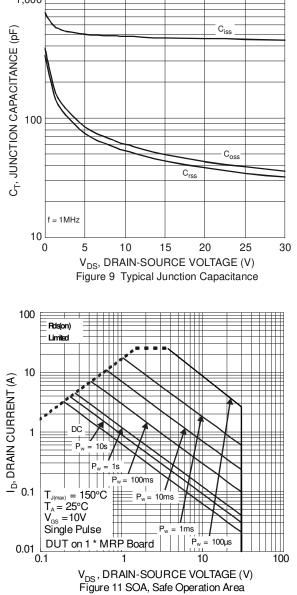


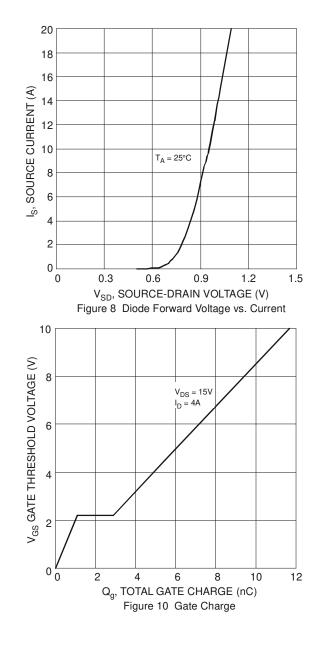




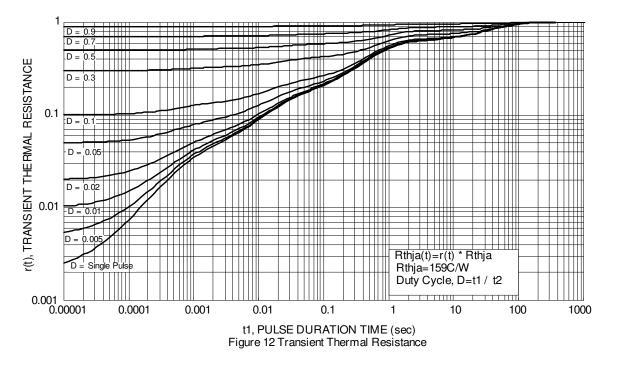






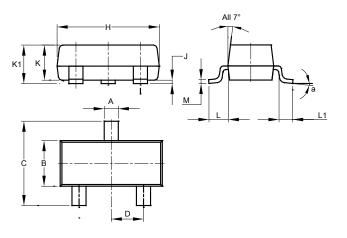






## Package Outline Dimensions

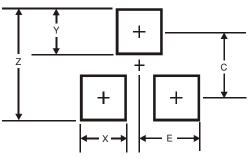
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
L	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
М	0.085	0.150	0.110			
а		8°				
All	Dimens	ions in	mm			

#### **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35



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